

IN THE CLAIMS:

1. (Previously Presented) A semiconductor device comprising:
  - a gate electrode formed over a substrate;
  - a gate insulating film formed over the gate electrode;
  - a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed there between, said semiconductor film including a channel formation region; and
    - source and drain regions comprising silicon formed on said semiconductor film, wherein a peak position of a Raman spectrograph of said semiconductor film is lower than  $520\text{ cm}^{-1}$ .
2. (Original) The semiconductor device according to claim 1 wherein said gate electrode comprises molybdenum.
3. (Original) The semiconductor device according to claim 1 wherein said gate insulating film comprises silicon oxide.
4. (Previously Presented) A semiconductor device comprising:
  - a gate electrode formed over a substrate;
  - a gate insulating film formed over the gate electrode;
  - a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed there between, said semiconductor film including a channel formation region; and
    - source and drain regions comprising silicon formed on said semiconductor film, wherein a peak position of a Raman spectrograph of said semiconductor film is lower than  $520\text{ cm}^{-1}$  and said semiconductor film has a distortion in the lattice.
5. (Original) The semiconductor device according to claim 4 wherein said gate electrode comprises molybdenum.

6. (Original) The semiconductor device according to claim 4 wherein said gate insulating film comprises silicon oxide.
7. (Currently Amended) A semiconductor device comprising:
  - a gate electrode formed over a substrate;
  - a gate insulating film formed over the gate electrode;
  - a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed therebetween, said semiconductor film including a channel formation region and
    - source and drain regions comprising silicon formed on said semiconductor film, wherein a peak position of a Raman spectrograph of said semiconductor film is lower than  $520\text{ cm}^{-1}$  and said semiconductor film has a distortion in the lattice, and the semiconductor film has no barrier against ~~earners~~ carriers at grain boundaries.
8. (Original) The semiconductor device according to claim 7 wherein said gate electrode comprises molybdenum.
9. (Original) The semiconductor device according to claim 7 wherein said gate insulating film comprises silicon oxide.
10. (Original) The semiconductor device according to claim 1 wherein said gate insulating film comprises silicon oxide containing fluorine.
11. (Original) The semiconductor device according to claim 4 wherein said gate insulating film comprises silicon oxide containing fluorine.
12. (Original) The semiconductor device according to claim 7 wherein said gate insulating film comprises silicon oxide containing fluorine.